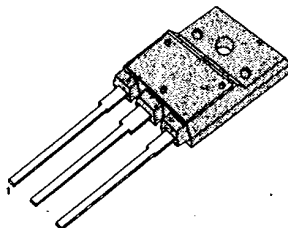


KSD5013**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR****COLOR TV HORIZONTAL OUTPUT
APPLICATIONS (DAMPER DIODE BUILT IN)**High Collector-Base Voltage $V_{CBO}=1500V$ **ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	1500	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	6	A
Collector Current (Peak)	I_C	16	A
Collector Dissipation ($T_c=25^\circ C$)	P_C	60	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

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TO-3P(F)

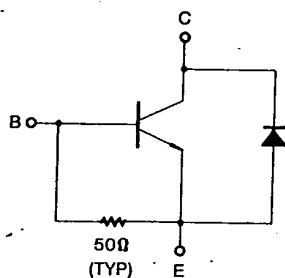


1. Base 2. Collector 3. Emitter

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ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$	40		130	mA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=1A$	8			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5A, I_B=1A$			5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5A, I_B=1A$			1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=1A$		3		MHz
Damper Diode Turn On Voltage	V_f	$I_f=6A$			2	V
Fall Time	t_f	$I_C=5A, I_{B1}=1A$ $I_{B2}=-2A, V_{CC}=200V$ $R_L=40\Omega$			0.4	μS

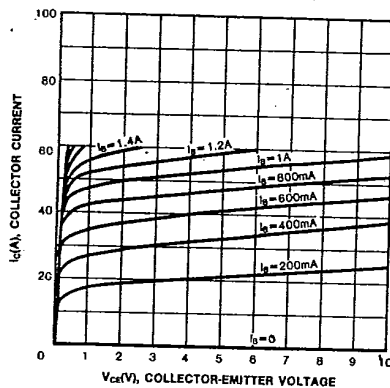


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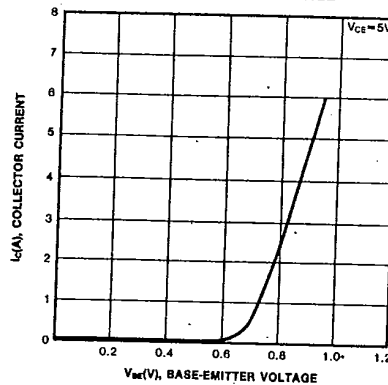
NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR

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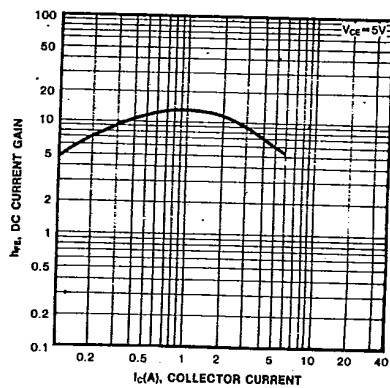
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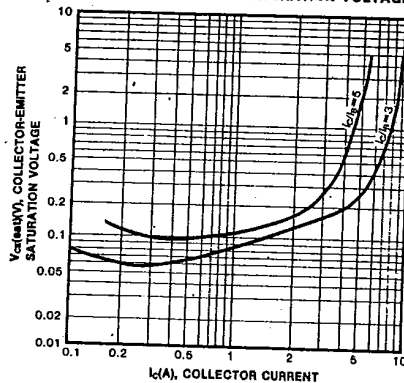
BASE-EMITTER ON VOLTAGE



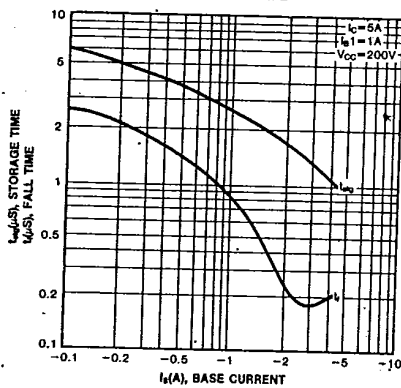
DC CURRENT GAIN



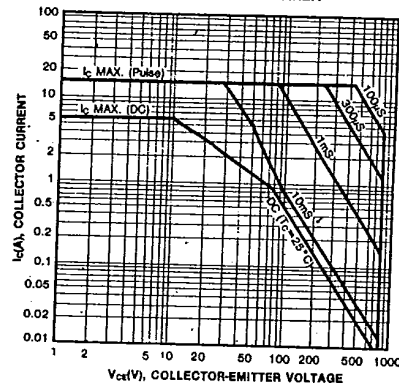
COLLECTOR-EMITTER SATURATION VOLTAGE



TURN ON TIME



SAFE OPERATING AREA



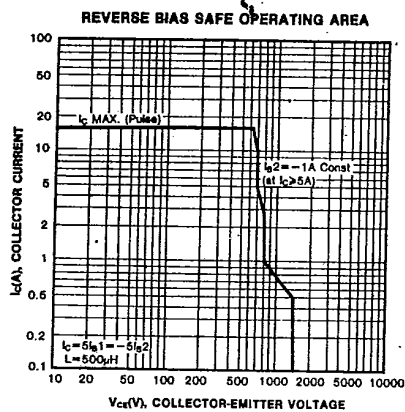
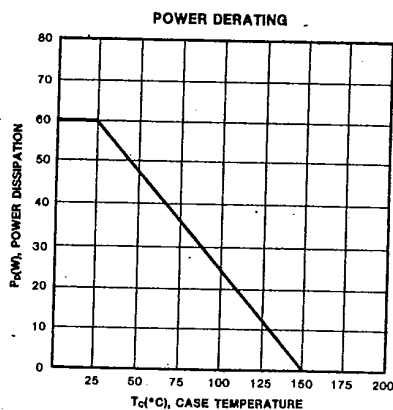
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**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR**

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KSD5014**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR**

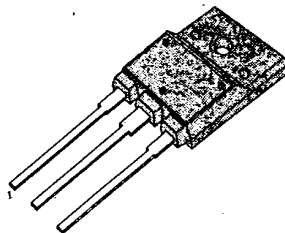
SAMSUNG SEMICONDUCTOR, INC.

T-33-11

**COLOR TV HORIZONTAL OUTPUT
APPLICATIONS**High Collector-Base Voltage $V_{CBO}=1500V$ **ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	1500	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	2.5	A
Collector Current (Peak)	I_C	10	A
Collector Dissipation ($T_C=25^\circ C$)	P_C	50	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	$-55 \sim 150$	$^\circ C$

TO-3P(F)



1. Base 2. Collector 3. Emitter

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			1	mA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=0.5A$	8			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=0.6A$			8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=0.6A$			1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.5A$		3		MHz
Fall Time	t_f	$I_C=2A, I_B1=0.6A$ $I_B2=-1.2A, R_L=100\Omega$			0.4	μS



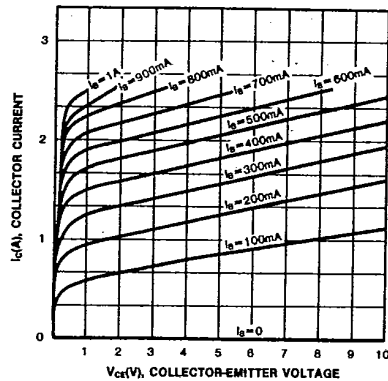
KSD5014

SAMSUNG SEMICONDUCTOR INC

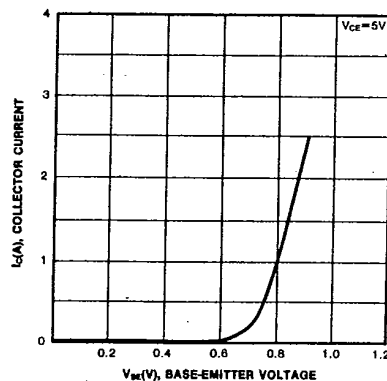
NPN TRIPLE DIFFUSED PLANAR SILICON TRANSISTOR

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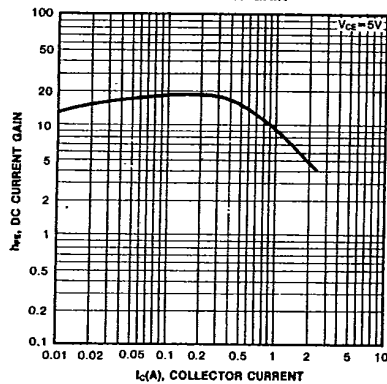
STATIC CHARACTERISTIC



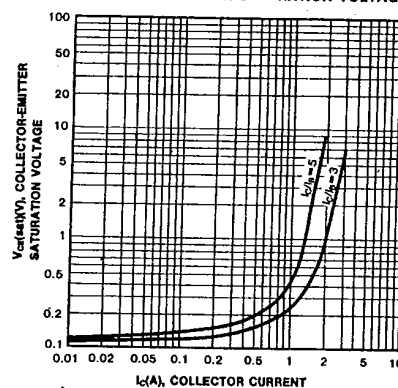
BASE-EMITTER ON VOLTAGE



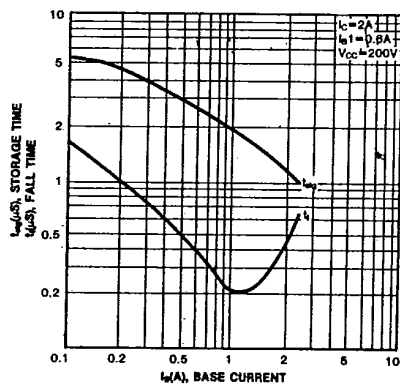
DC CURRENT GAIN



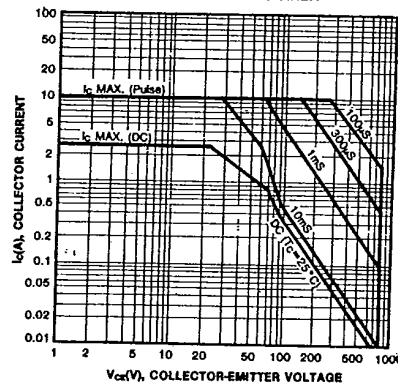
COLLECTOR-EMITTER SATURATION VOLTAGE



TURN ON TIME



SAFE OPERATING AREA



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**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR**

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